

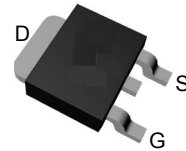
Features

- -150V/-25A,
 $R_{DS(ON)} = 120m\Omega(\text{typ.}) @ V_{GS} = -10V$
 $R_{DS(ON)} = 131m\Omega(\text{typ.}) @ V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

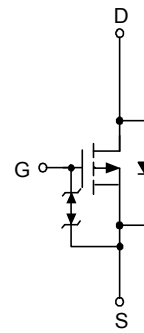
Applications

- Power Management for Industrial DC / DC Converters.

Pin Configuration



Top View of TO-252-2



P-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-150	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-25	A
I _D	Continuous Drain Current	T _C =25°C	-25	A
		T _C =100°C	-10	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-75	
P _D	Maximum Power Dissipation	T _C =25°C	54	W
		T _C =100°C	21.7	
R _{θJC}	Thermal Resistance-Junction to Case		2.3	°C/W
I _D	Continuous Drain Current	T _A =25°C	-3.5	A
		T _A =70°C	-2.8	
P _D	Maximum Power Dissipation	T _A =25°C	2.5	W
		T _A =70°C	1.6	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient		50	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	-14	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	49	mJ

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Note c : Surface Mounted on 1in^2 pad area.

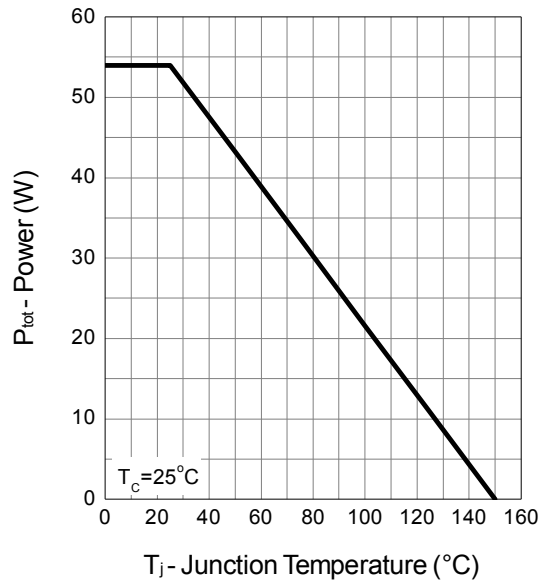
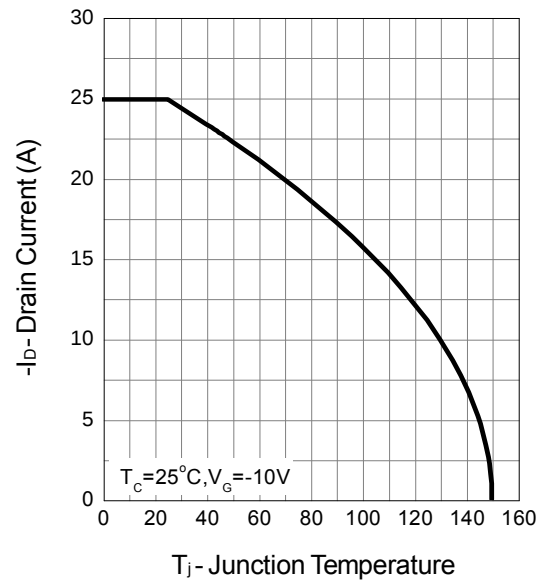
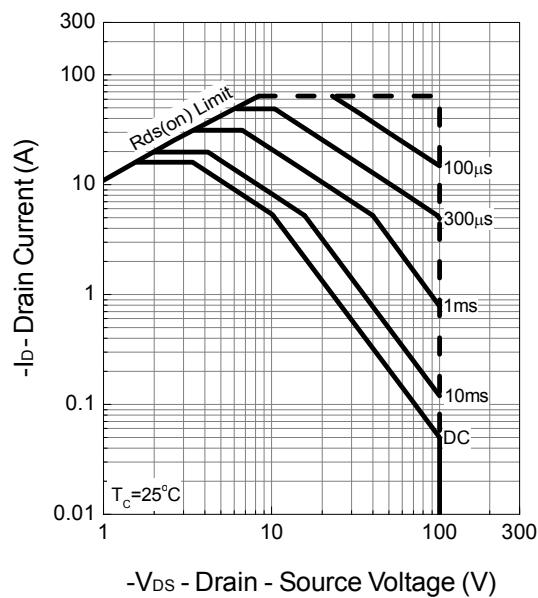
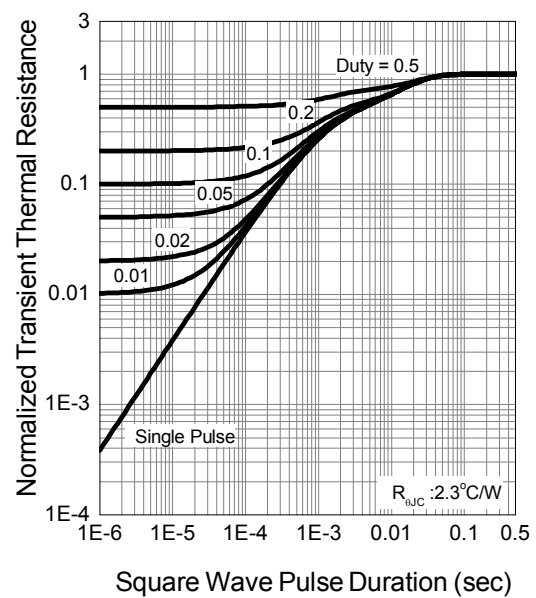
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-150	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-120V, V _{GS} =0V T _J =85°C	-	-	-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.5	-1.9	-3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-20A V _{GS} =-4.5V, I _{DS} =-20A	-	120 131	150 160	mΩ mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-9A, dI _{SD} /dt=100A/μs	-	36	-	ns
Q _{rr}	Reverse Recovery Charge		-	57	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	8.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	7370	7780	pF
C _{oss}	Output Capacitance		-	127	-	
C _{rss}	Reverse Transfer Capacitance		-	116	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	11	20	ns
t _r	Turn-on Rise Time		-	9	17	
t _{d(OFF)}	Turn-off Delay Time		-	83	150	
t _f	Turn-off Fall Time		-	39	71	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-4.5V, I _{DS} =-9A	-	15	-	
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _{DS} =-9A	-	32	45	
Q _{gs}	Gate-Source Charge		-	5	-	
Q _{gd}	Gate-Drain Charge		-	7	-	

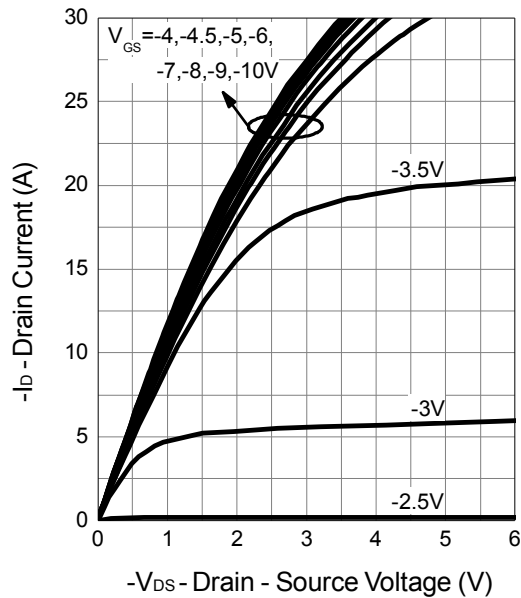
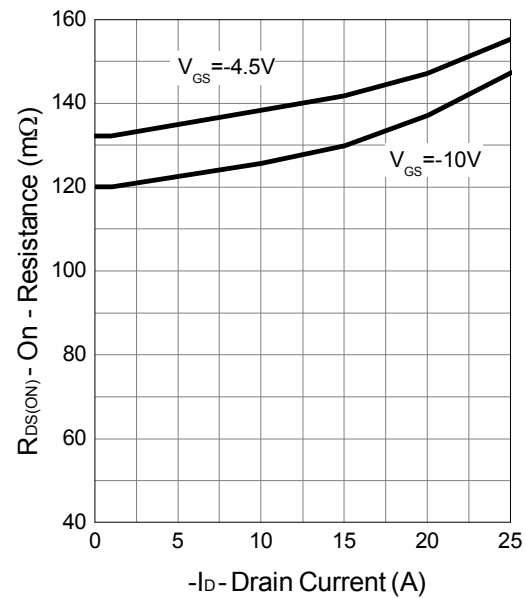
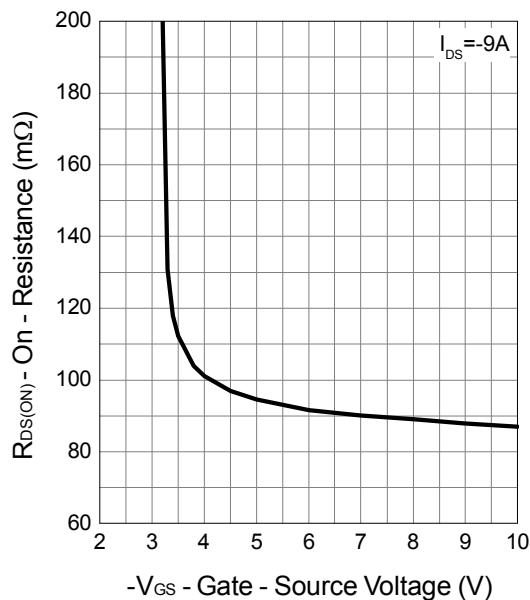
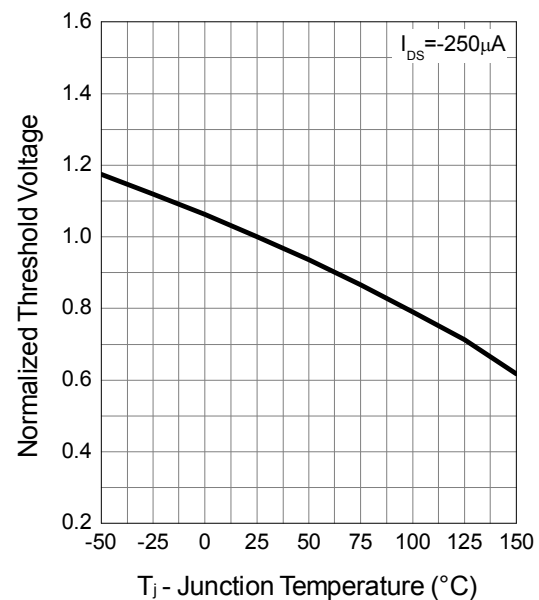
Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note e : Guaranteed by design, not subject to production testing.

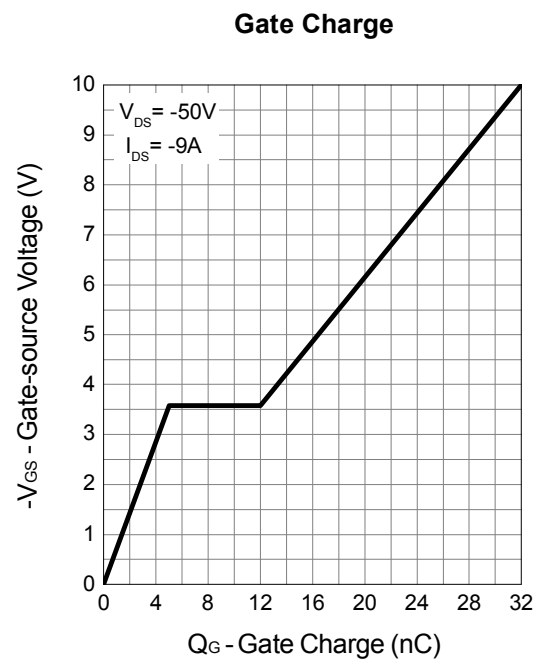
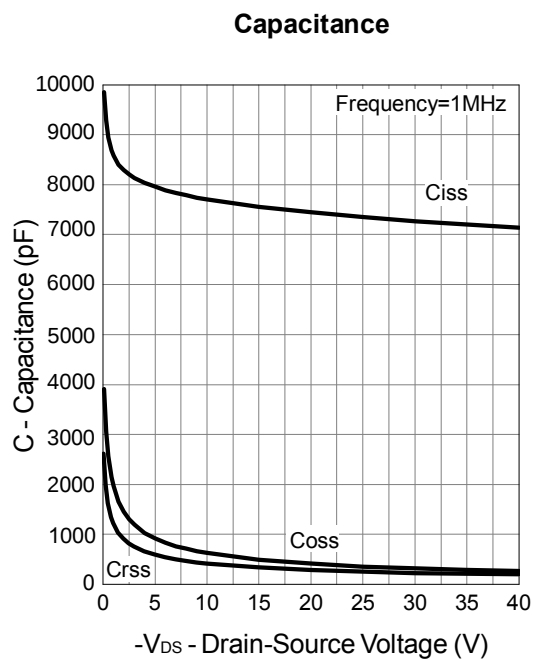
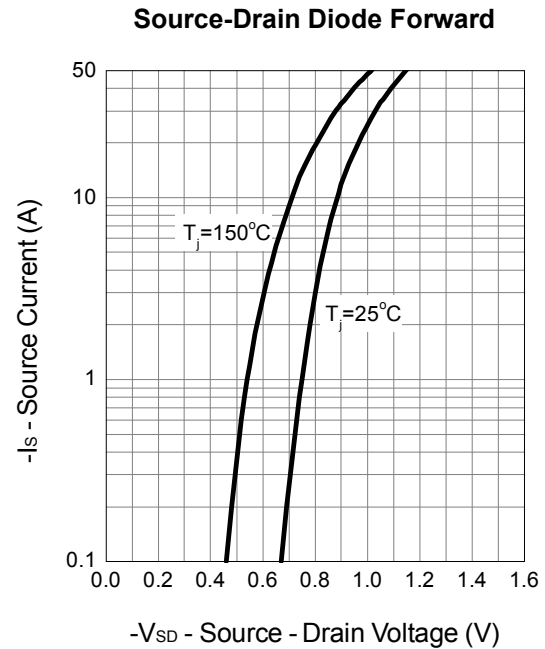
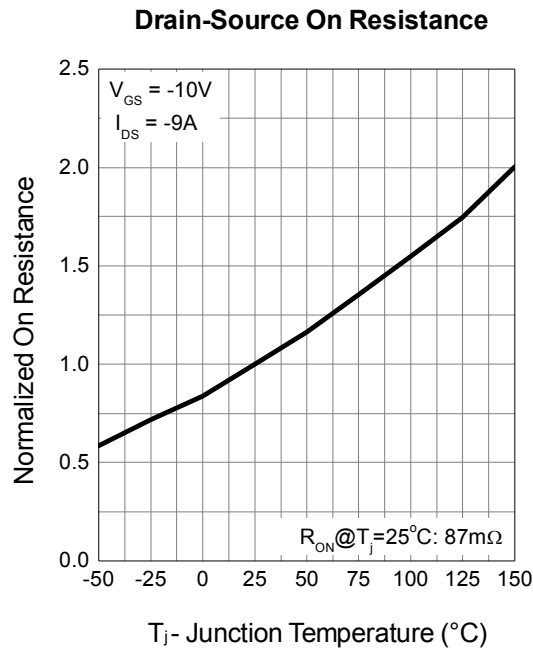
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


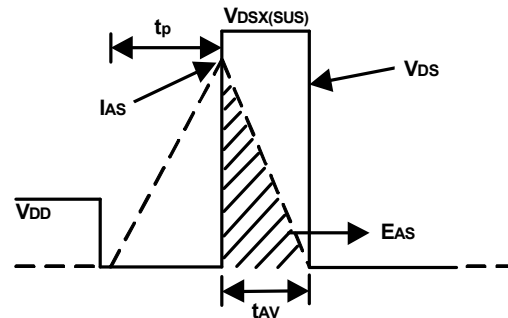
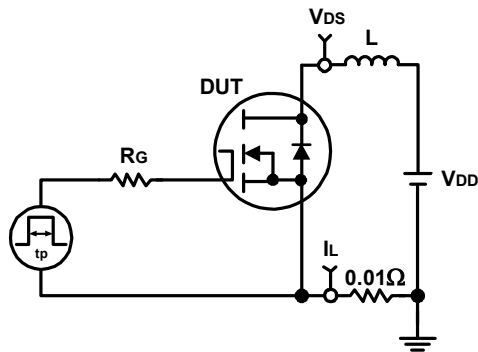
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


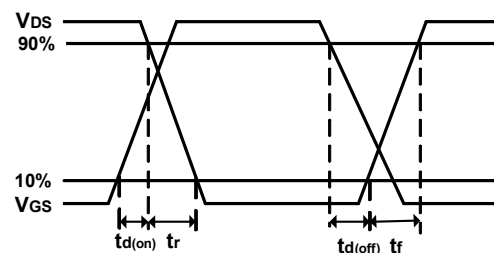
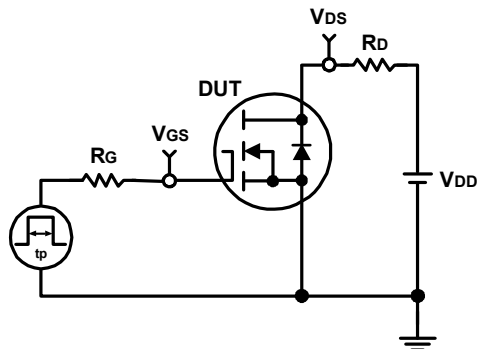
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

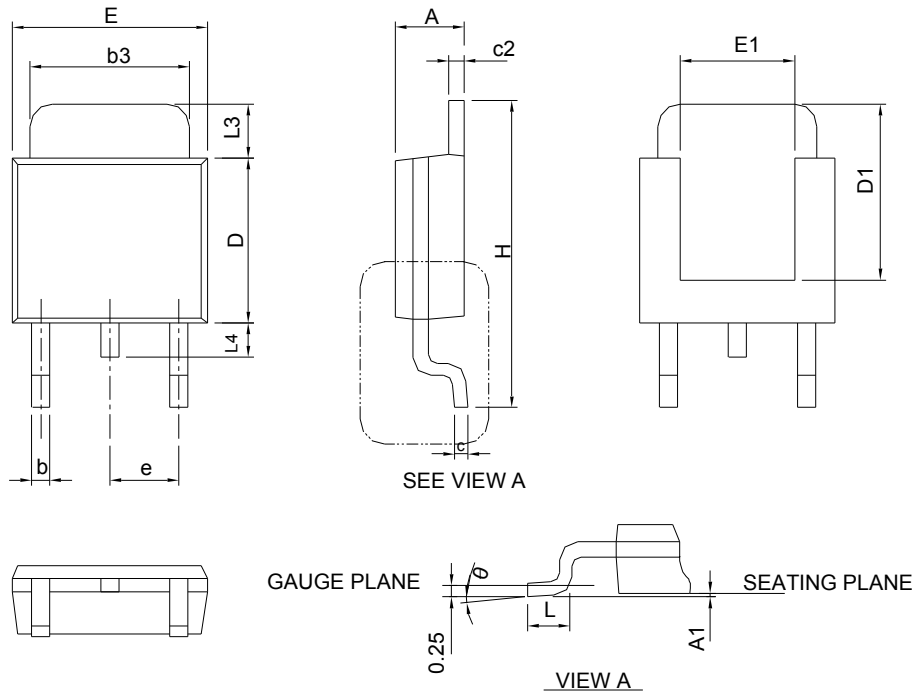


Switching Time Test Circuit and Waveforms



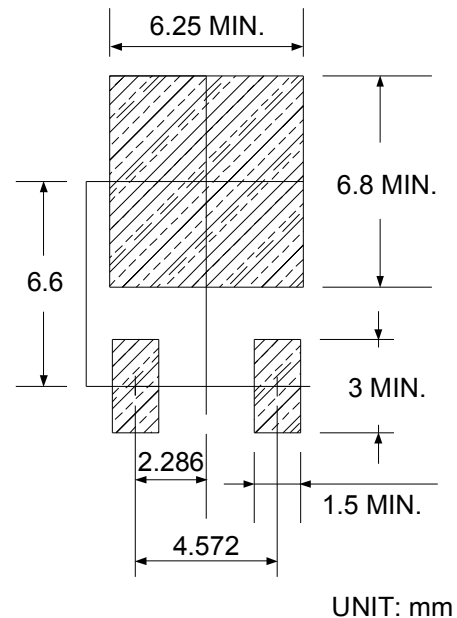
Package Information

TO-252-2



SYMBOL	TO-252-2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



Note : Follow JEDEC TO-252 .